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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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Silicon NPN Epitaxial Planar



ADE-208-1481 (Z)

Rev.0 Feb. 2002

Features

• VHF amplifier, local oscillator

Outline

СМРАК		
	3 2 1	1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	30	V	
Collector to emitter voltage	V _{CEO}	20	V	
Emitter to base voltage	V _{EBO}	4	V	
Collector current	I _c	20	mA	
Collector power dissipation	P _c *	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

*Value on the glass epoxy board (10 mm x 10 mm x 0.7 mm)

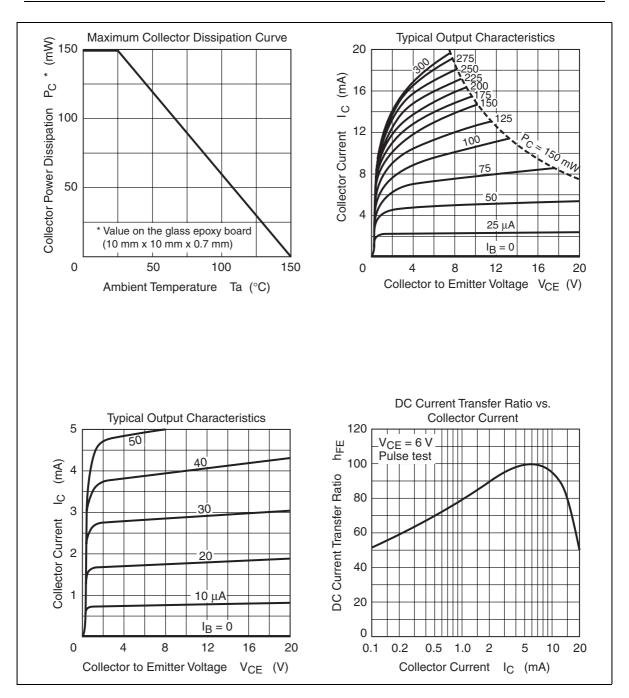
Electrical Characteristics

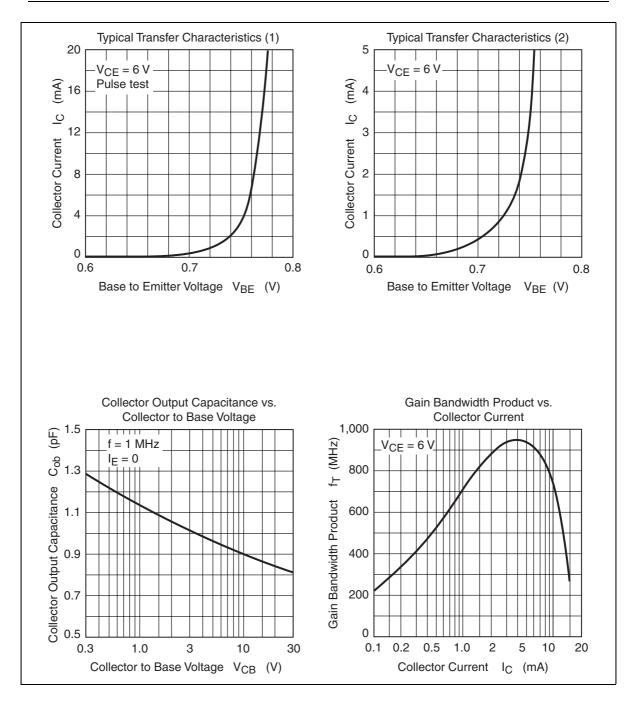
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\scriptscriptstyle (BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\scriptscriptstyle (BR)CEO}$	20	—	—	V	$I_{c} = 1 \text{ mA}, \text{ R}_{BE} = \infty$
Emitter to base breakdown voltage	$V_{\scriptscriptstyle (BR)EBO}$	4	—	—	V	$I_{_{\rm E}} = 10 \ \mu A, \ I_{_{\rm C}} = 0$
Collector cutoff current	I _{ceo}			0.5	μA	$V_{ce} = 10 \text{ V}, \text{ R}_{be} = \infty$
Emitter cutoff current	I _{ebo}	_	_	0.5	μA	$V_{_{\rm EB}} = 2 \text{ V}, \text{ I}_{_{\rm C}} = 0$
DC current transfer ratio	h_{FE}^{*1}	60	_	200	_	$V_{ce} = 6 V, I_{c} = 1 mA$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.17	_	V	$I_{c} = 20 \text{ mA}, I_{B} = 4 \text{ mA}$
Base to emitter voltage	V_{BE}	_	0.72	_	V	$V_{ce} = 6 \text{ V}, \text{ I}_{c} = 1 \text{ mA}$
Gain bandwidth product	f _T	_	940		MHz	$V_{ce} = 6V, I_{c} = 5 \text{ mA}$
Collector output capacitance	C _{ob}		0.9		pF	$V_{_{CB}} = 10 \text{ V}, \text{ I}_{_{E}} = 0, \text{ f} = 1 \text{ MHz}$

Notes: 1. The 2SC5852 is grouped by h_{FE} as follows.

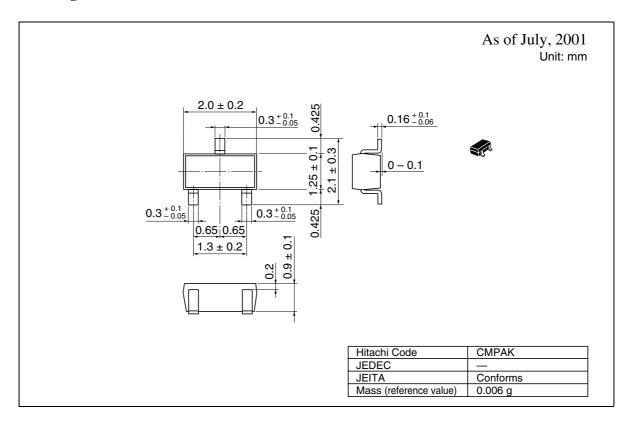
Grade	В	С
Mark	QB	QC
$h_{_{FE}}$	60 to 120	100 to 200





RENESAS

Package Dimensions





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Colophon 5.0

